

Features

- · High Blocking Voltage with Low On-Resistance
- · High Speed Switching with Low capacitances
- · Avalanche Ruggednes

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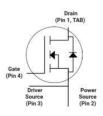
TO-263-7L Package

Applications

- · Solar Inverters
- · Switch Mode Power Supplies
- · Auxiliary power supplies
- · Smart meters

Ordering Part Number	Package	e Marking	
HC3M001K170J	TO-263-7L	HC3M001K170J	

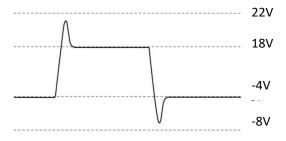




Maximum Ratings ($T_c = 25$ °C unless otherwise specifed)

Parameter	Symbol	Value	Unit
Drain-source voltage	Vos	1700	V
Continuous drain current Tc = 25°C Tc = 100°C	lo	6.7 5	А
Pulsed drain current (Tc = 25°C, tp limited by T _{jmax})	ID pulse	16.7	А
Avalanche energy, single pulse (L=10mH)	Eas	1000	mJ
Gate-Source voltage	Vgs	-4/+18	V
Gate-Source voltage(dynamic,Absolute maximum values)	VGSmax	-8/+22	V
Power dissipation (Tc = 25°C)	Ptot	86	W
Operating junction and storage temperature	T _j , T _{stg}	-55+175	°C

• Example of acceptable Vgs waveform





Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction - case. Max	RthJC	1.7	°C/W
Thermal resistance, junction – ambient. Max	RthJA	40	O/ V V

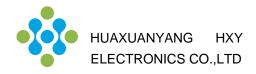
Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	neter Symbol Val	Value		Unit	Test Condition	
rai ailletei	Syllibol	min.	typ.	max.	Offic	rest Condition
Static Characteristic						
Drain-source breakdown voltage	BVpss	1700	-	-	V	Vgs=0V, Ib=100uA
Gate threshold voltage	VGS(th)	1.8	3	4.5	V	Vps=Vgs,Ip=380uA
Zero gate voltage drain current	loss	-	1 5	10 -	μА	V _{DS} =1700V,V _{GS} =0V T _j =25°C T _j =175°C
Gate-source leakage current	Igss	-		100	nA	Vgs=20V,Vps=0V
Drain-source on-state resistance	RDS(on)	-	700 1280	910 -	m	Vgs=18V,Ip=1A, Tj=25°C Tj=175°C
Dynamic Characteristic	•		•	•	•	
Input Capacitance	Ciss	-	285	-		V _{DS} = 1000V
Output Capacitance	Coss	-	15.3	-	pF	Vgs = 0V T _J = 25°C
Reverse Transfer Capacitance	Crss	-	2.2	-		V _{AC} = 25mV f = 1MHz
Gate Total Charge	QG	-	16.5	-		Vps =1000V
Gate-Source charge	Qgs	-	2.7	-	nC	Vgs =-5/18V Ip =1A
Gate-Drain charge	Qgd	-	12.5	-		ID = IA
Turn-On Switching Energy	Еом	•	73.9	-	μJ	
Turn-Off Switching Energy-	Eoff	-	20.4		μυ	VDD =1000V
Turn-on delay time	t d(on)	-	6.2	-		Vgs = -3.5/+18V Ip =2A
Rise time	tr	-	13.7	-	ns	Rg =10
Turn-off delay time	td(off)	-	9.4	-	119	L=1880uH
Fall time	t f	-	45.4	-		
Gate resistance	Rg	-	18	-		Vac = 25mV, f=1MHz



Body Diode Characteristic

Parameter	Symbol Value Unit Te	Value Unit Test Condition	Value			
l arameter		rest condition				
Body Diode Forward Voltage	Vsp		4		V	Vgs=0V,Isp=1A, TJ=25°C
Body Diode Forward Voltage		Vgs=0V,Isp=1A, T _J =175°C				
Body Diode Reverse Recovery Time	trr	-	33.5	-	ns	$V_R = 1000V$, $V_{GS} = -3.5V/+18V$ $I_D = 2A, R_g = 30$
Body Diode Reverse Recovery Charge	Qrr	-	56.1	-	nC	di/dt = 1000A/µS L = 1880uH



Typical Performance Characteristics

Fig 1. Output Characteristic (T_J=-55°C)

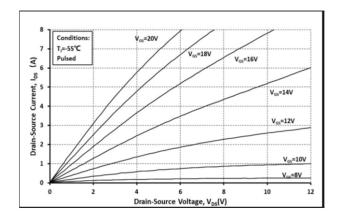


Fig 2. Output Characteristic (T_J=25℃)

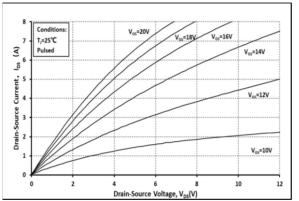


Fig 3. Output Characteristic (T_J=175℃)

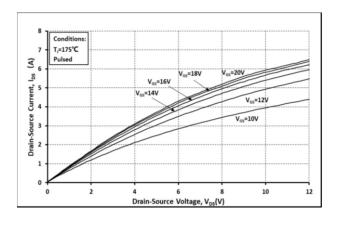


Fig 4: Rdson Vs Ids Characteristic

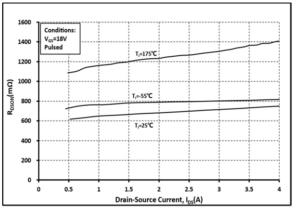


Fig 5: Rds(on) vs. Temperature

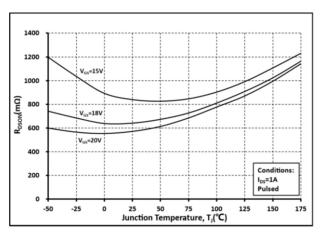


Fig 6: Transfer Characteristic

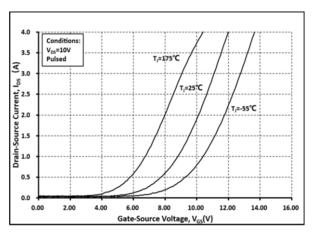




Fig 7: Body-diode Characteristic (T_J=-55°C)

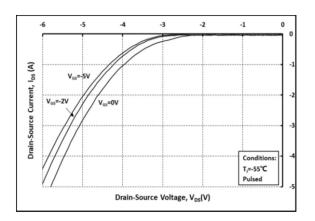


Fig 8: Body-diode Characteristic (T_J=25℃)

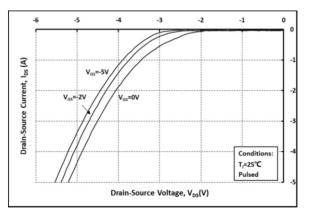


Fig 9: Body-diode Characteristic (T_J=175℃)

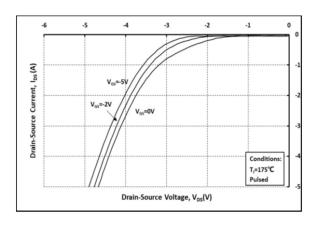


Fig 10: V_{TH} Vs T_J Temperature Characteristic

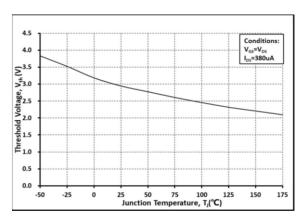


Fig 11: Gate Charge Characteristics

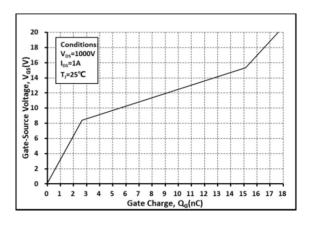


Fig 12: 3rd Quadrant Characteristic(T_J=-55°C)

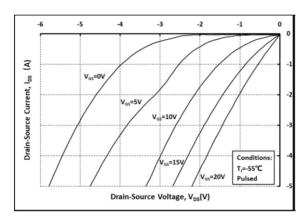


Fig 13: 3rd Quadrant Characteristic(T_J=25°C)

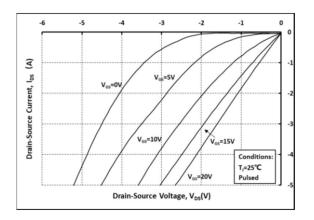


Fig 14: 3rd Quadrant Characteristic(T_J=175℃)

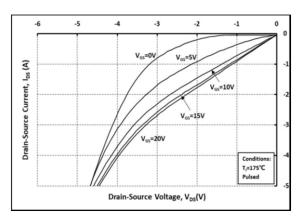


Fig 15: Capacitance Characteristic

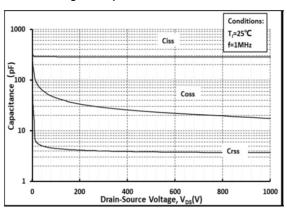


Fig 16: Safe Operating Area

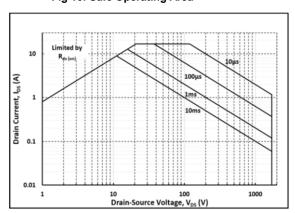
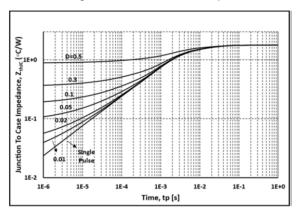
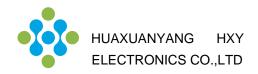


Fig 17: Transient Thermal Impedance





Test Circuit Schematic

Figure A. Definition of switching times

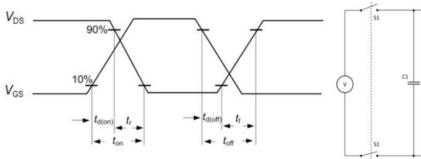


Figure B. Dynamic test circuit

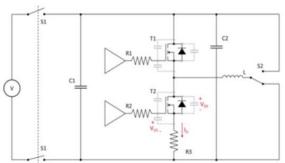


Figure C. Definition of body diodeswitching characteristics

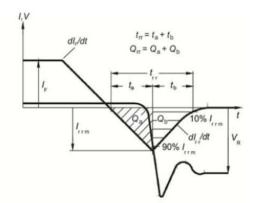
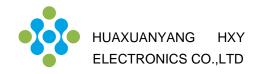
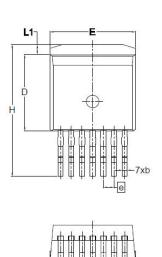


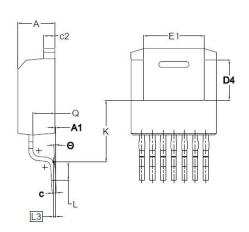
Figure C. Definition of diode switching characteristics



Package Dimensions

Package TO-263-7L





SYMBOL	DIMENSIONS				
	MIN.	NOM.	MAX.		
A	4.30	4.40	4.50		
A1	0.00	0.10	0.25		
b	0.50	0.60	0.70		
С	0.45	0.50	0.60		
c2	1.20	1.30	1.40		
D	8.93	9.08	9.23		
D4	4.65	4.80	4.95		
E	10.08	10.18	10.28		
E1	6.82	7.22	7.62		
e	1.27 BSC				
н	15.00	15.70	16.00		
к	7.30				
L	1.90	2.20	2.50		
L1	1.00	1.20	1.40		
L3	0.25 BSC				
Q	2.45	2.60	2.75		
Θ	0°	3°	7°		

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